



SOT-23 Plastic-Encapsulate Transistors

MMBTA64 TRANSISTOR (PNP)

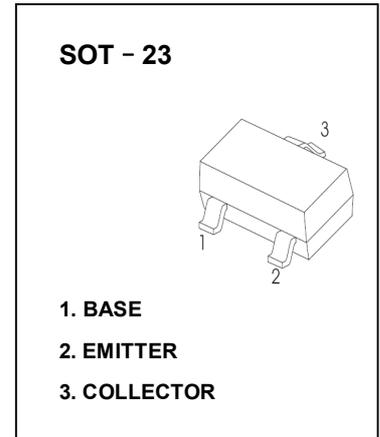
FEATURES

- For Applications Requiring High Current Gain

MARKING:2V

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-10	V
I _C	Collector Current	-800	mA
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	416	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-10			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-10V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =-5V, I _C =-10mA	10			K
	h _{FE(2)} *	V _{CE} =-5V, I _C =-100mA	20			K
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-100mA, I _B =-0.1mA			-1.5	V
Base-emitter voltage	V _{BE} *	V _{CE} =-5V, I _C =-100mA			-2	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz	125			MHz

*Pulse test: pulse width ≤300μs, duty cycles ≤ 2.0%.